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Vishay Siliconix

N-Channel 150 V (D-S) MOSFET

PRODUCT	SUMMARY		
V _{DS} (V)	R _{DS(on)} (Ω) MAX.	I _D (A)	Q _g (TYP.)
150	0.0090 at V _{GS} = 10 V	128	63 nC
150	0.0105 at V _{GS} = 7.5 V	119	



Ordering Information:

SUM80090E-GE3 (lead (Pb)-free and halogen-free)

FEATURES

- ThunderFET® power MOSFET
- Maximum 175 °C junction temperature
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



APPLICATIONS

- Power supplies:
 - Uninterruptible power supplies
 - AC/DC switch-mode power supplies
 - Lighting
- Synchronous rectification
- DC/DC converter
- · Motor drive switch
- DC/AC inverter
- Solar micro inverter

- N-Channel MOSFET
- Class D audio amplifier
- · Battery management

ABSOLUTE MAXIMUM RATINGS	$(T_C = 25 ^{\circ}C, \text{ unless othe})$	rwise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	150	V
Gate-Source Voltage		V _{GS}	± 20	v
Continuous Proin Current /T 150 °C	T _C = 25 °C		128	
Continuous Drain Current (T _J = 150 °C)	T _C = 125 °C	I _D	74	A
Pulsed Drain Current (t = 100 μs)		I _{DM}	240	^
Avalanche Current	L = 0.1 mH	I _{AS}	60	
Single Avalanche Energy ^a	L=0.1 mn	E _{AS}	180	mJ
Mayimum Daway Dissinction 3	T _C = 25 °C	В	375 ^b	W
Maximum Power Dissipation ^a	T _C = 125 °C	P _D	125 ^b	vv
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W
Junction-to-Case (Drain)	R _{thJC}	0.4	C/VV

Notes

- a. Duty cycle $\leq 1 \%$.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).



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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	150	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	2	-	5	v	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 250	nA	
		V _{DS} = 150 V, V _{GS} = 0 V	-	-	1	μА	
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} = 150 V, V_{GS} = 0 V, T_J = 125 °C	-	-	100		
		V _{DS} = 150 V, V _{GS} = 0 V, T _J = 175 °C	-	-	2	mA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	90	-	-	Α	
Duain Caluma On State Resistance 2		V _{GS} = 10 V, I _D = 30 A	-	0.0075	0.0090	0	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 7.5 \text{ V}, I_D = 30 \text{ A}$	-	0.0084	0.0105	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 30 A	-	52	-	S	
Dynamic ^b							
Input Capacitance	C _{iss}		-	3425	-		
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 75 \text{ V}, f = 1 \text{ MHz}$	-	535	-	pF	
Reverse Transfer Capacitance	C _{rss}		-	26	-	 	
Total Gate Charge ^c	Qg		-	63	95		
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 75 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 60 \text{ A}$	-	19.5	-	nC	
Gate-Drain Charge ^c	Q_{gd}		-	20.5	-	nC	
Gate Resistance	R_g	f = 1 MHz	1.5	3	5	Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	15	30		
Rise Time ^c	t _r	$V_{DD} = 75 \text{ V}, R_L = 1.25 \Omega$	-	114	220		
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 60 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	28	56	ns	
Fall Time ^c	t _f		-	8	16		
Drain-Source Body Diode Ratings ar	nd Characteri	stics ^b (T _C = 25 °C)					
Pulsed Current (t = 100 μs)	I _{SM}		-	-	240	Α	
Forward Voltage ^a	V _{SD}	I _F = 30 A, V _{GS} = 0 V	-	0.73	1.2	V	
Reverse Recovery Time	t _{rr}		-	110	220	ns	
Peak Reverse Recovery Charge	I _{RM(REC)}	$I_F = 30 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	10	20	Α	
Reverse Recovery Charge	Q _{rr}		-	0.5	1	μC	

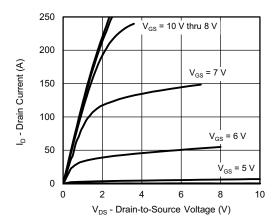
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

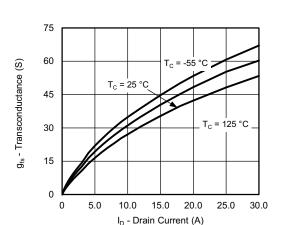
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



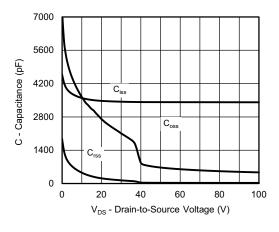
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



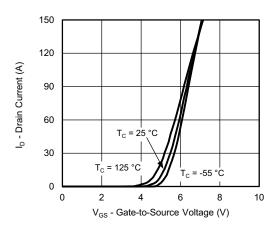
Output Characteristics



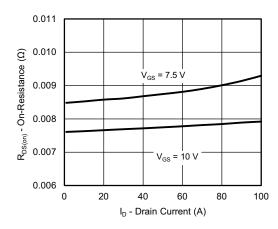
Transconductance



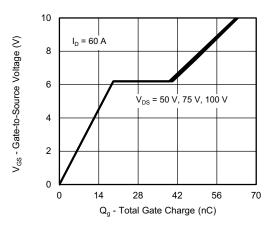
Capacitance



Transfer Characteristics



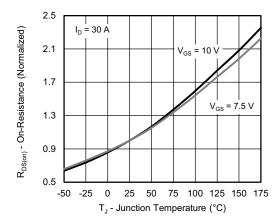
On-Resistance vs. Drain Current



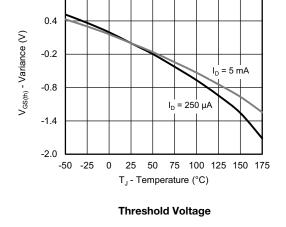
Gate Charge



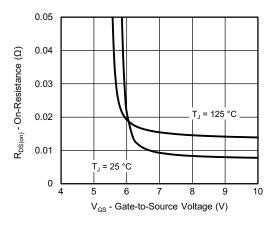
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



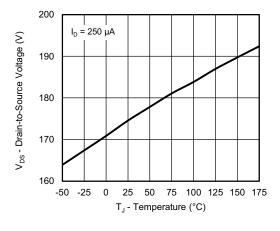
On-Resistance vs. Junction Temperature



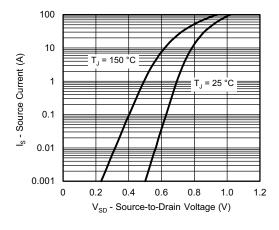
1.0



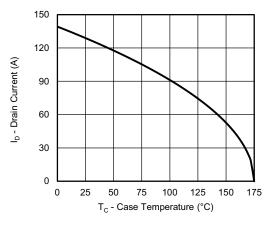
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature



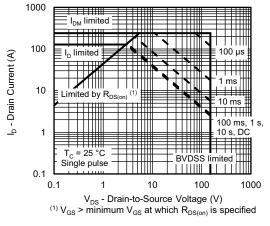
Source Drain Diode Forward Voltage

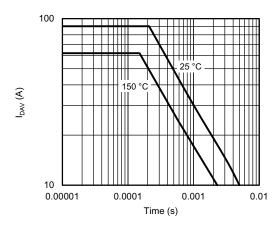


Current De-Rating



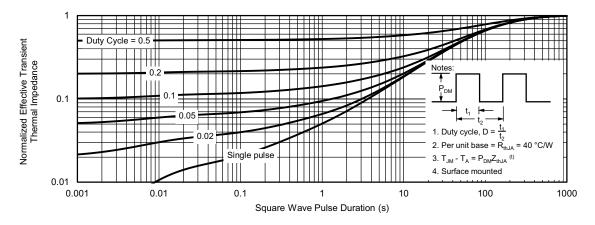
THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)





Safe Operating Area

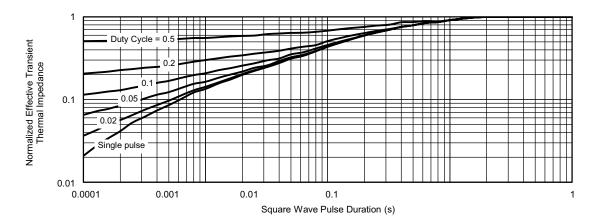
I_{DAV} vs. Time



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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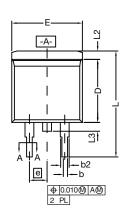
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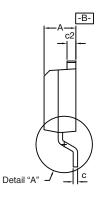


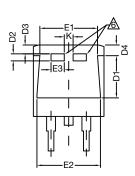
TO-263 (D²PAK): 3-LEAD

VERSION 1: FACILITY CODE = T

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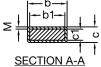








DETAIL A (ROTATED 90°)



< <u> </u>	
2 T 7 7 0	
SECTION A-A	

Notes

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6. This feature is for thick lead.

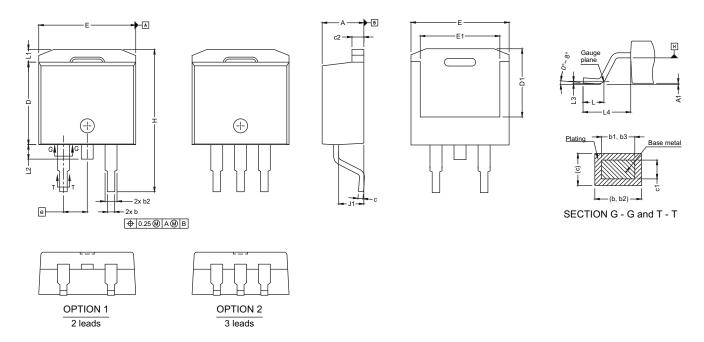
		INC	HES	MILLIN	METERS
	DIM.	MIN.	MAX.	MIN.	MAX.
А		0.160	0.190	4.064	4.826
	b	0.020	0.039	0.508	0.990
	b1	0.020	0.035	0.508	0.889
	b2	0.045	0.055	1.143	1.397
c*	Thin lead	0.013	0.018	0.330	0.457
C	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
CI	Thick lead	0.023	0.027	0.584	0.685
	c2	0.045	0.055	1.143	1.397
	D	0.340	0.380	8.636	9.652
	D1	0.220	0.240	5.588	6.096
D2		0.038	0.042	0.965	1.067
	D3	0.045	0.055	1.143	1.397
	D4	0.044	0.052	1.118	1.321
	E	0.380	0.410	9.652	10.414
	<u>E1</u>	0.245	-	6.223	-
E2		0.355	0.375	9.017	9.525
E3		0.072	0.078	1.829	1.981
	е	0.100) BSC	2.54	BSC
	K	0.045	0.055	1.143	1.397
L		L 0.575		14.605	15.875
L1		L1 0.090		2.286	2.794
L2		0.040	0.055	1.016	1.397
	L3	0.050	0.070	1.270	1.778
	L4	0.010	BSC	0.254	BSC
	М	-	0.002	-	0.050



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VERSION 2: FACILITY CODE = N



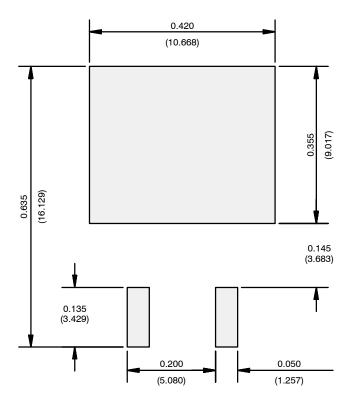
DIM.	MIN.	MAX.	
A	4.36	4.56	
A1	0	0.25	
b	0.70	0.90	
b1	0.51	0.89	
b2	1.20	1.46	
b3	1.17	1.37	
С	0.38	0.694	
c1	0.38	0.534	
c2	1.19	1.34	
D	8.60	9.00	
D1	6.9	7.5	
E	10.15	10.55	
E1	8.1	8.7	
е	2.54	BSC	
Н	15.0	15.6	
L	1.9	2.5	
L1	-	1.65	
L2	-	1.78	
L3	0.25	5 typ.	
L4	4.78	5.28	
J1	2.56	2.96	

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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